



General Description

The ZM027N03N combines advanced trench MOSFET technology with a low resistance package to provide extremely low R\_DS(ON) . This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
R\_DS(ON) to minimize conductive loss

Application

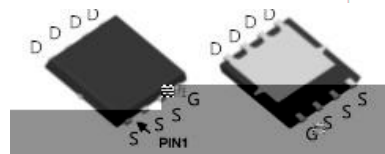
nd Synchronous Rectifier

Product Summary



4

2



Ordering Information:

Table with 2 columns and 4 rows containing ordering information such as part numbers and reel tape quantities.

Absolute Maximum Ratings T\_C =25

Table with 4 columns: Parameter, Symbol, Rating, and Unit. Lists various electrical ratings like Drain-Source Voltage, Gate-Source Voltage, and Currents.







Fig.7 Switching Time Measurement Circuit

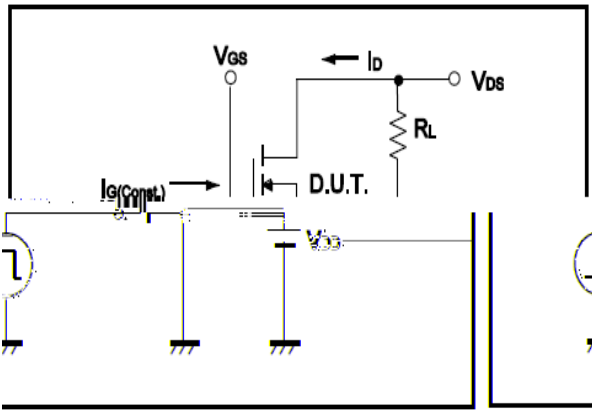


Fig.8 Gate Charge Waveform

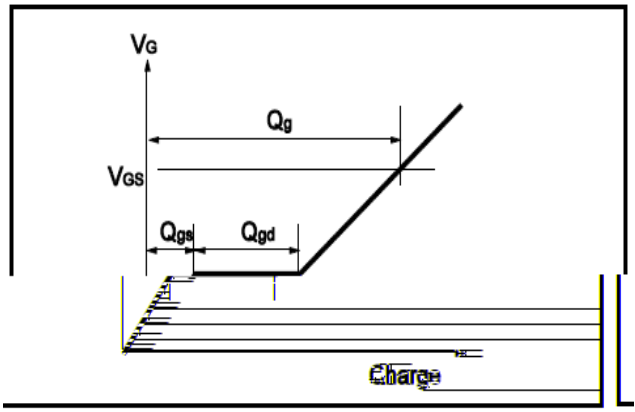


Fig.9 Switching Time Measurement Circuit

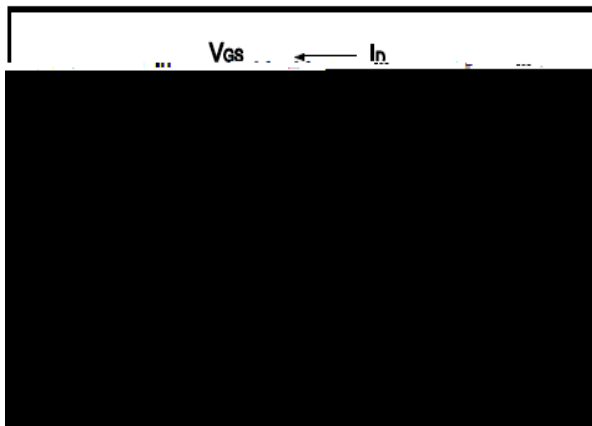


Fig.10 Gate Charge Waveform

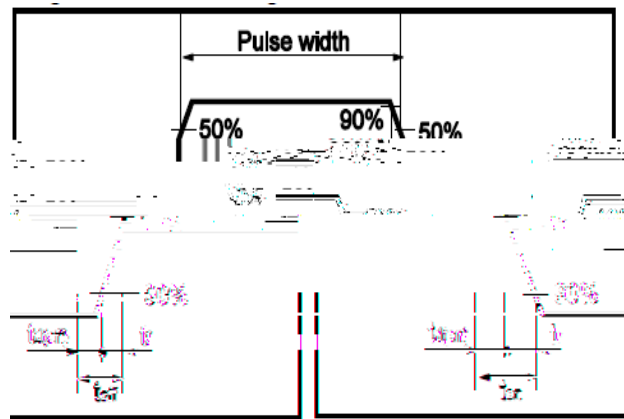


Fig.11 Avalanche Measurement Circuit

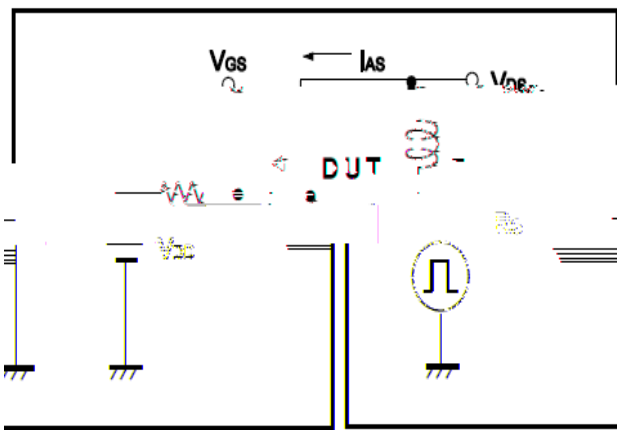
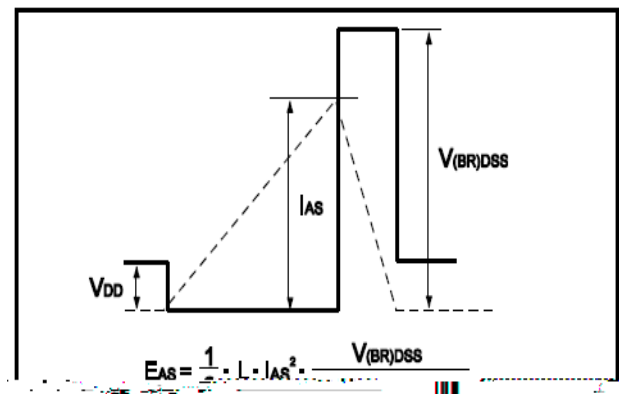


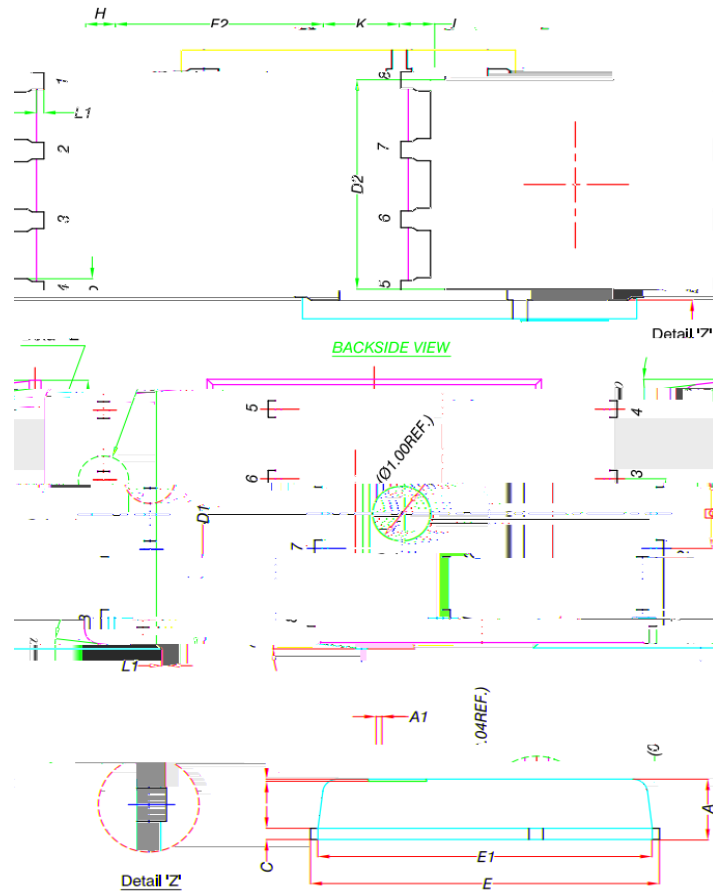
Fig.12 Avalanche Waveform





Dimensions DFN5x6

Unit mm



| DIM. | MILLIMETERS |      |      |
|------|-------------|------|------|
|      | MIN.        | NOM. | MAX. |
| A    | 0.90        | 1.00 | 1.10 |
| A1   | 0           | -    | 0.05 |
| b    | 0.33        | 0.41 | 0.51 |
| C    | 0.20        | 0.25 | 0.30 |
| D1   | 4.80        | 4.90 | 5.00 |
| D2   | 3.61        | 3.81 | 3.96 |

